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# STB20N65M5, STI20N65M5, STP20N65M5, STW20N65M5

N-channel 650 V, 0.160  $\Omega$  typ., 18 A MDmesh™ V Power MOSFET  
in D<sup>2</sup>PAK, I<sup>2</sup>PAK, TO-220 and TO-247 packages

Datasheet — production data

## Features

Order codes	V <sub>DS</sub> @ T <sub>Jmax</sub>	R <sub>DS(on)</sub> max	I <sub>D</sub>
STB20N65M5	710 V	0.19 $\Omega$	18 A
STI20N65M5			
STP20N65M5			
STW20N65M5			

- Worldwide best R<sub>DS(on)</sub> \* area
- Higher V<sub>DSS</sub> rating and high dv/dt capability
- Excellent switching performance
- 100% avalanche tested

## Applications

- Switching applications

## Description

These devices are N-channel MDmesh™ V Power MOSFETs based on an innovative proprietary vertical process technology, which is combined with STMicroelectronics' well-known PowerMESH™ horizontal layout structure. The resulting product has extremely low on-resistance, which is unmatched among silicon-based Power MOSFETs, making it especially suitable for applications which require superior power density and outstanding efficiency.

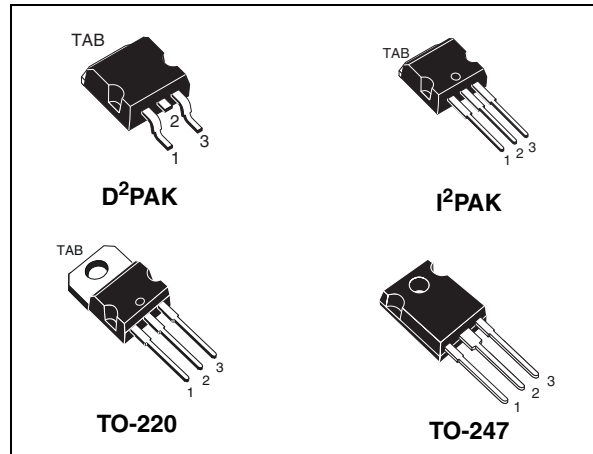


Figure 1. Internal schematic diagram

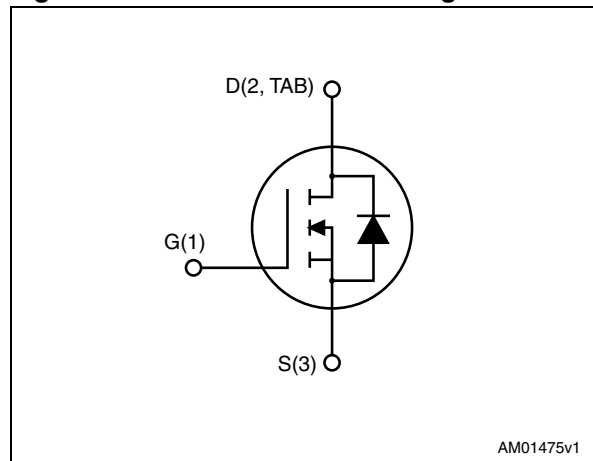


Table 1. Device summary

Order codes	Marking	Package	Packaging
STB20N65M5	20N65M5	D <sup>2</sup> PAK	Tape and reel
STI20N65M5		I <sup>2</sup> PAK	Tube
STP20N65M5		TO-220	
STW20N65M5		TO-247	

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# 1 Electrical ratings

**Table 2. Absolute maximum ratings**

Symbol	Parameter	Value	Unit
$V_{GS}$	Gate-source voltage	$\pm 25$	V
$I_D$	Drain current (continuous) at $T_C = 25\text{ }^\circ\text{C}$	18	A
$I_D$	Drain current (continuous) at $T_C = 100\text{ }^\circ\text{C}$	11.3	A
$I_{DM}^{(1)}$	Drain current (pulsed)	72	A
$P_{TOT}$	Total dissipation at $T_C = 25\text{ }^\circ\text{C}$	130	W
$dv/dt^{(1)}$	Peak diode recovery voltage slope	15	V/ns
$T_{stg}$	Storage temperature	- 55 to 150	$^\circ\text{C}$
$T_j$	Max. operating junction temperature	150	$^\circ\text{C}$

1.  $I_{SD} \leq 18\text{ A}$ ,  $di/dt \leq 400\text{ A}/\mu\text{s}$ ;  $V_{DS\text{ peak}} < V_{(BR)DSS}$ ,  $V_{DD}=400\text{ V}$

**Table 3. Thermal data**

Symbol	Parameter	Value			Unit
		D <sup>2</sup> PAK	I <sup>2</sup> PAK, TO-220	TO-247	
$R_{thj-case}$	Thermal resistance junction-case max	0.96			$^\circ\text{C}/\text{W}$
$R_{thj-amb}$	Thermal resistance junction-ambient max		62.5	50	$^\circ\text{C}/\text{W}$
$R_{thj-pcb}^{(1)}$	Thermal resistance junction-pcb max	30			$^\circ\text{C}/\text{W}$

1. When mounted on 1 inch<sup>2</sup> FR-4, 1 Oz copper board.

**Table 4. Avalanche characteristics**

Symbol	Parameter	Value	Unit
$I_{AR}$	Avalanche current, repetitive or not repetitive (pulse width limited by $T_{jmax}$ )	4	A
$E_{AS}$	Single pulse avalanche energy (starting $t_j=25\text{ }^\circ\text{C}$ , $I_d=I_{AR}$ ; $V_{dd}=50\text{ V}$ )	270	mJ

## 2 Electrical characteristics

( $T_C = 25\text{ °C}$  unless otherwise specified)

**Table 5. On /off states**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$I_D = 1\text{ mA}$ , $V_{GS} = 0$	650			V
$I_{DSS}$	Zero gate voltage drain current ( $V_{GS} = 0$ )	$V_{DS} = 650\text{ V}$ $V_{DS} = 650\text{ V}$ , $T_C = 125\text{ °C}$			1 100	$\mu\text{A}$ $\mu\text{A}$
$I_{GSS}$	Gate-body leakage current ( $V_{DS} = 0$ )	$V_{GS} = \pm 25\text{ V}$			$\pm 100$	nA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}$ , $I_D = 250\text{ }\mu\text{A}$	3	4	5	V
$R_{DS(on)}$	Static drain-source on-resistance	$V_{GS} = 10\text{ V}$ , $I_D = 9\text{ A}$		0.160	0.19	$\Omega$

**Table 6. Dynamic**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$C_{iss}$	Input capacitance	$V_{DS} = 100\text{ V}$ , $f = 1\text{ MHz}$ , $V_{GS} = 0$	-	1434	-	pF
$C_{oss}$	Output capacitance			38		pF
$C_{rss}$	Reverse transfer capacitance			3.7		pF
$C_{o(tr)}^{(1)}$	Equivalent capacitance time related	$V_{DS} = 0\text{ to }520\text{ V}$ , $V_{GS} = 0$	-	118	-	pF
$C_{o(er)}^{(2)}$	Equivalent capacitance energy related			35		pF
$R_G$	Intrinsic gate resistance	$f = 1\text{ MHz}$ open drain	-	3.5	-	$\Omega$
$Q_g$	Total gate charge	$V_{DD} = 520\text{ V}$ , $I_D = 9\text{ A}$ , $V_{GS} = 10\text{ V}$ (see <a href="#">Figure 18</a> )	-	36	-	nC
$Q_{gs}$	Gate-source charge			7.5		nC
$Q_{gd}$	Gate-drain charge			18		nC

1. Time related is defined as a constant equivalent capacitance giving the same charging time as  $C_{oss}$  when  $V_{DS}$  increases from 0 to 80%  $V_{DSS}$
2. Energy related is defined as a constant equivalent capacitance giving the same stored energy as  $C_{oss}$  when  $V_{DS}$  increases from 0 to 80%  $V_{DSS}$



**Table 7. Switching times**

Symbol	Parameter	Test conditions	Min.	Typ.	Max	Unit
$t_{d(v)}$	Voltage delay time	$V_{DD} = 400\text{ V}$ , $I_D = 12\text{ A}$ ,		43		ns
$t_{r(v)}$	Voltage rise time	$R_G = 4.7\ \Omega$ , $V_{GS} = 10\text{ V}$	-	7.5	-	ns
$t_{f(i)}$	Current fall time	(see <a href="#">Figure 19</a> and		7.5		ns
$t_{c(off)}$	Crossing time	<a href="#">Figure 22</a> )		11.5		ns

**Table 8. Source drain diode**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$I_{SD}$	Source-drain current		-		18	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)		-		72	A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 18\text{ A}$ , $V_{GS} = 0$	-		1.5	V
$t_{rr}$	Reverse recovery time	$I_{SD} = 18\text{ A}$ , $di/dt = 100\text{ A}/\mu\text{s}$	-	288		ns
$Q_{rr}$	Reverse recovery charge	$V_{DD} = 100\text{ V}$ (see <a href="#">Figure 22</a> )		4		$\mu\text{C}$
$I_{RRM}$	Reverse recovery current			27		A
$t_{rr}$	Reverse recovery time	$I_{SD} = 18\text{ A}$ , $di/dt = 100\text{ A}/\mu\text{s}$	-	342		ns
$Q_{rr}$	Reverse recovery charge	$V_{DD} = 100\text{ V}$ , $T_j = 150\text{ }^\circ\text{C}$		4.7		$\mu\text{C}$
$I_{RRM}$	Reverse recovery current	(see <a href="#">Figure 22</a> )		28		A

1. Pulse width limited by safe operating area.

2. Pulsed: pulse duration = 300  $\mu\text{s}$ , duty cycle 1.5%

## 2.1 Electrical characteristics (curves)

Figure 2. Safe operating area for D<sup>2</sup>PAK, I<sup>2</sup>PAK, TO-220

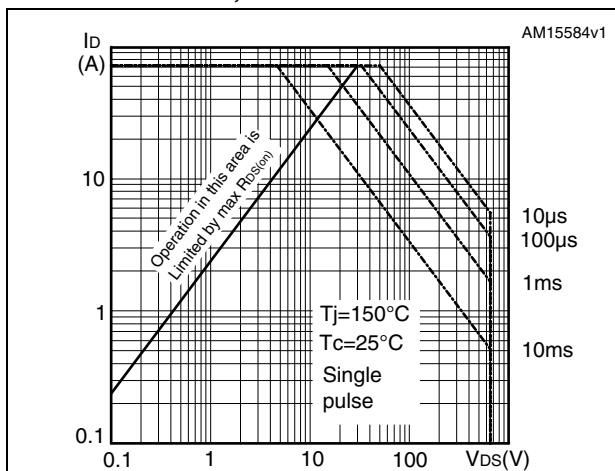


Figure 3. Thermal impedance for D<sup>2</sup>PAK, I<sup>2</sup>PAK, TO-220

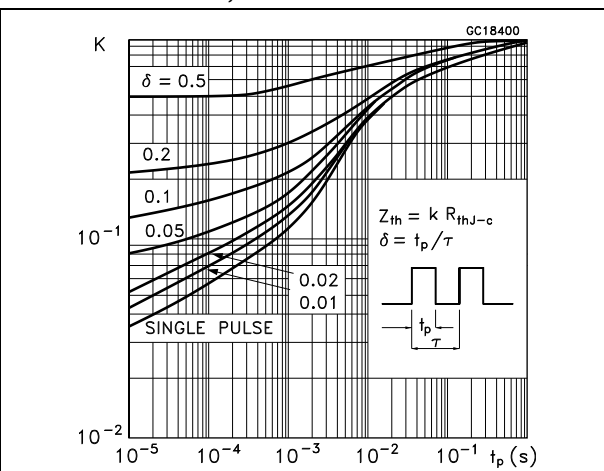


Figure 4. Safe operating area for TO-247

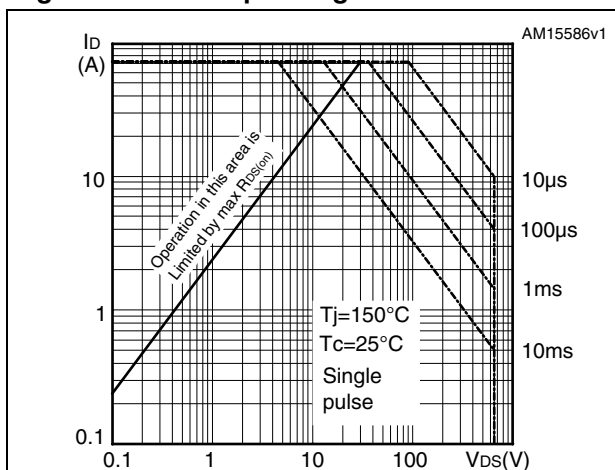


Figure 5. Thermal impedance for TO-247

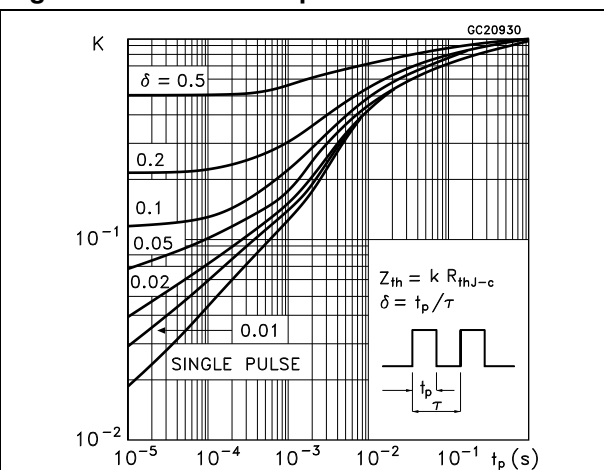


Figure 6. Output characteristics

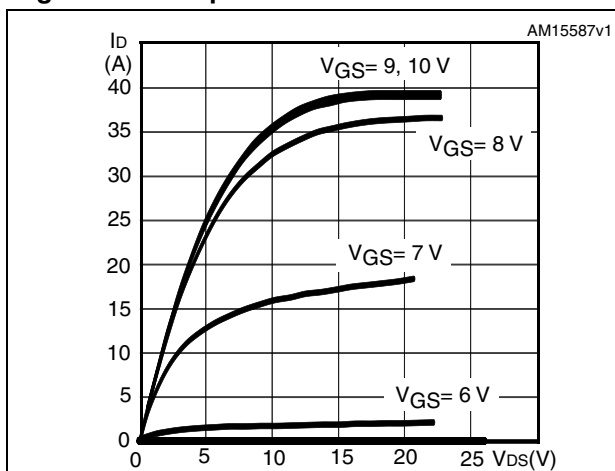


Figure 7. Transfer characteristics

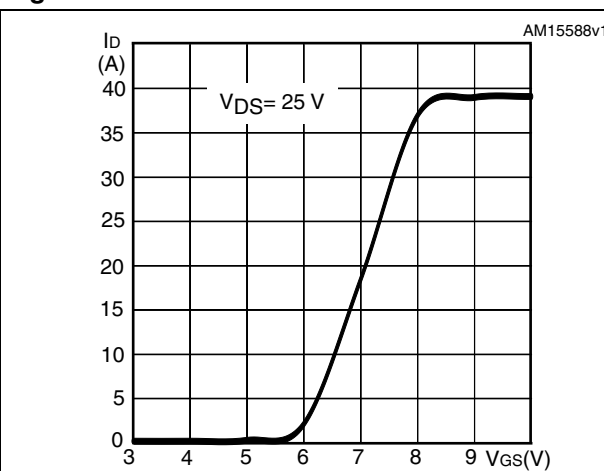


Figure 8. Gate charge vs gate-source voltage Figure 9. Static drain-source on-resistance

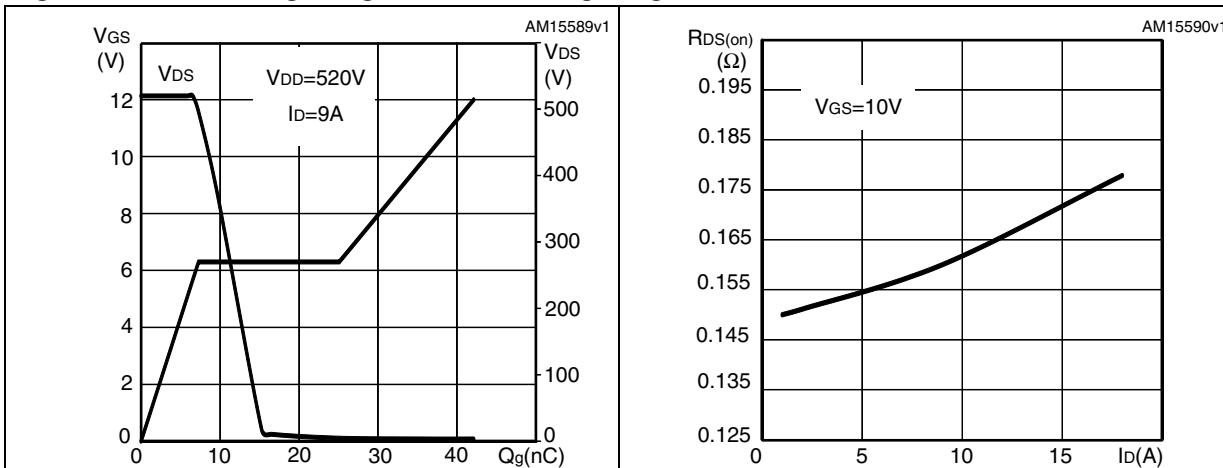


Figure 10. Capacitance variations Figure 11. Output capacitance stored energy

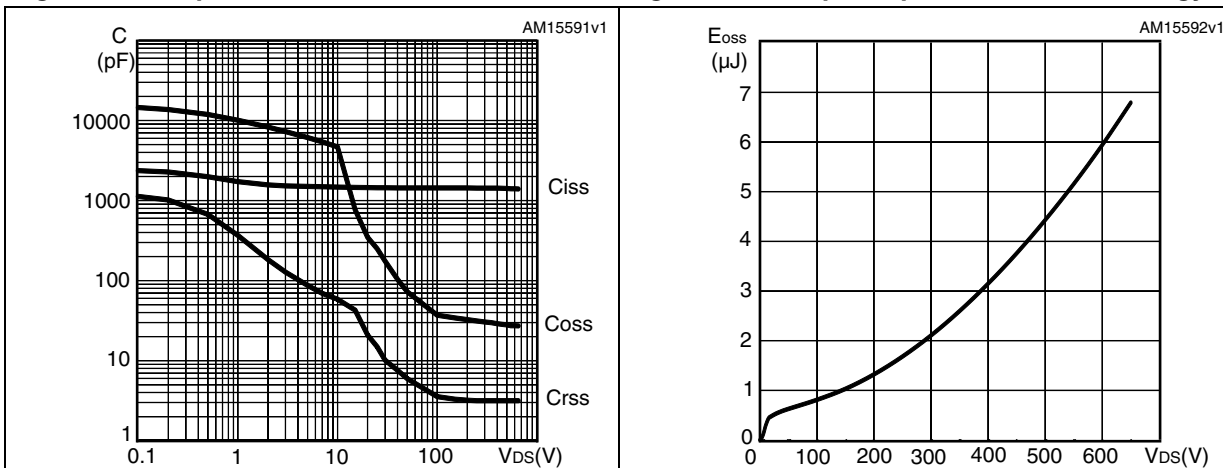


Figure 12. Normalized gate threshold voltage vs temperature Figure 13. Normalized on-resistance vs temperature

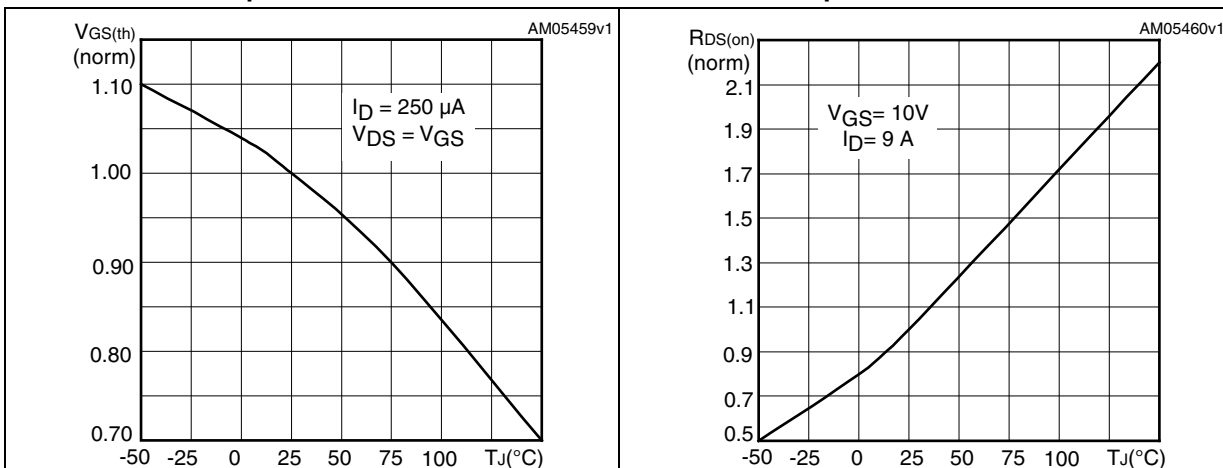




Figure 14. Normalized  $B_{V_{DSS}}$  vs temperature

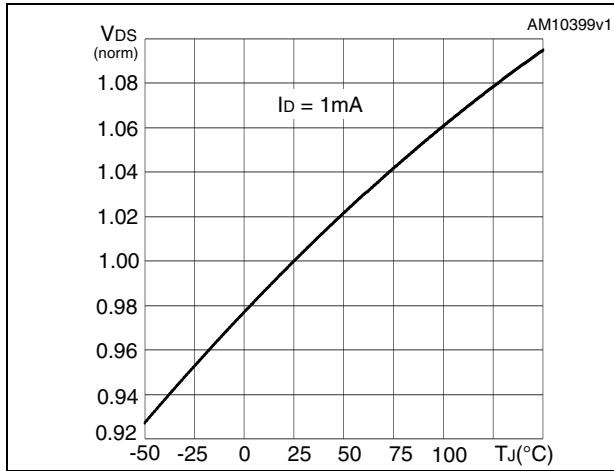


Figure 15. Drain-source diode forward characteristics

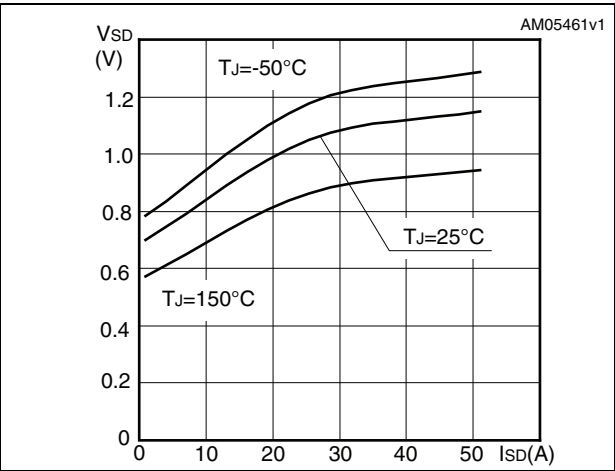
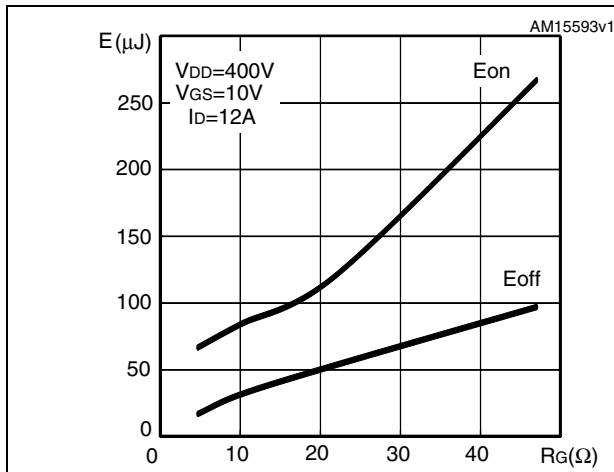


Figure 16. Switching losses vs gate resistance (1)



1.  $E_{on}$  including reverse recovery of a SiC diode

### 3 Test circuits

Figure 17. Switching times test circuit for resistive load

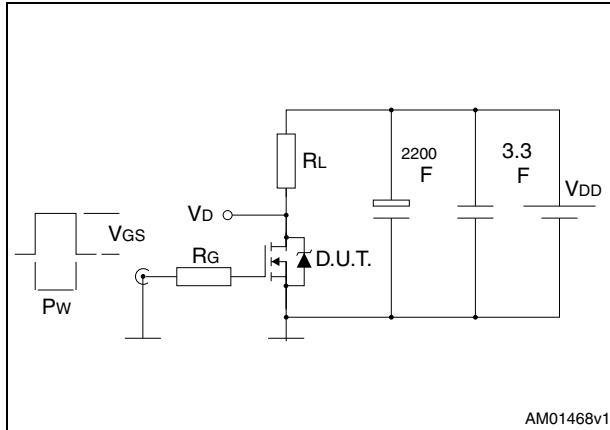


Figure 18. Gate charge test circuit

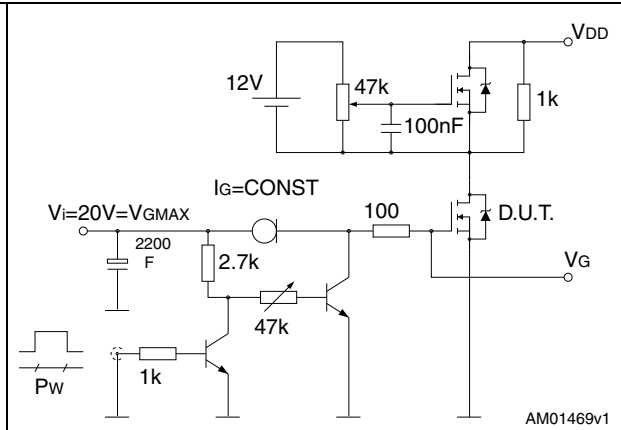


Figure 19. Test circuit for inductive load switching and diode recovery times

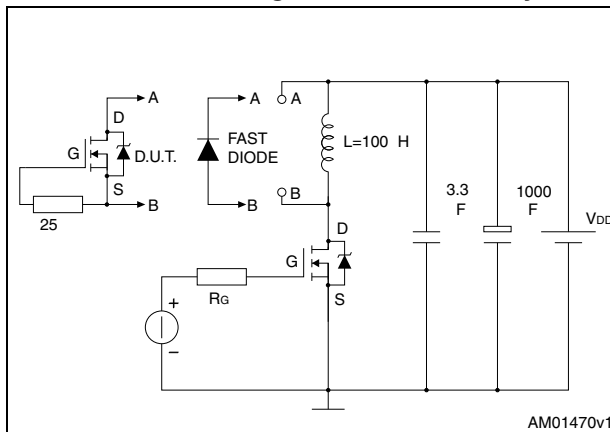


Figure 20. Unclamped inductive load test circuit

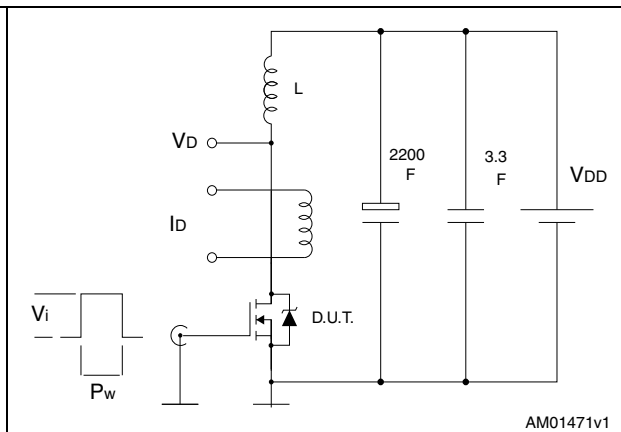


Figure 21. Unclamped inductive waveform

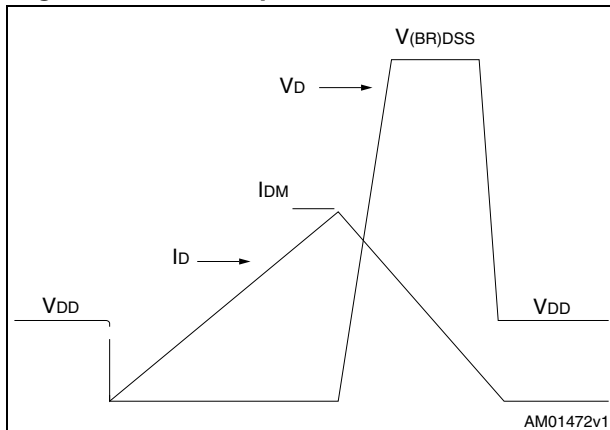
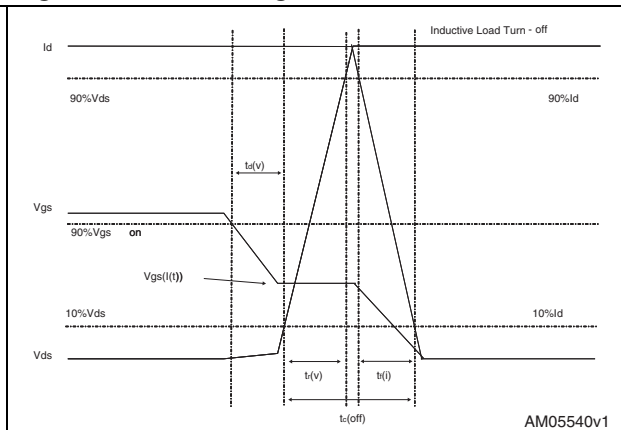


Figure 22. Switching time waveform



## 4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK<sup>®</sup> packages, depending on their level of environmental compliance. ECOPACK<sup>®</sup> specifications, grade definitions and product status are available at: [www.st.com](http://www.st.com). ECOPACK<sup>®</sup> is an ST trademark.

Table 9. D<sup>2</sup>PAK (TO-263) mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
A1	0.03		0.23
b	0.70		0.93
b2	1.14		1.70
c	0.45		0.60
c2	1.23		1.36
D	8.95		9.35
D1	7.50		
E	10		10.40
E1	8.50		
e		2.54	
e1	4.88		5.28
H	15		15.85
J1	2.49		2.69
L	2.29		2.79
L1	1.27		1.40
L2	1.30		1.75
R		0.4	
V2	0°		8°

Figure 23. D<sup>2</sup>PAK (TO-263) drawing

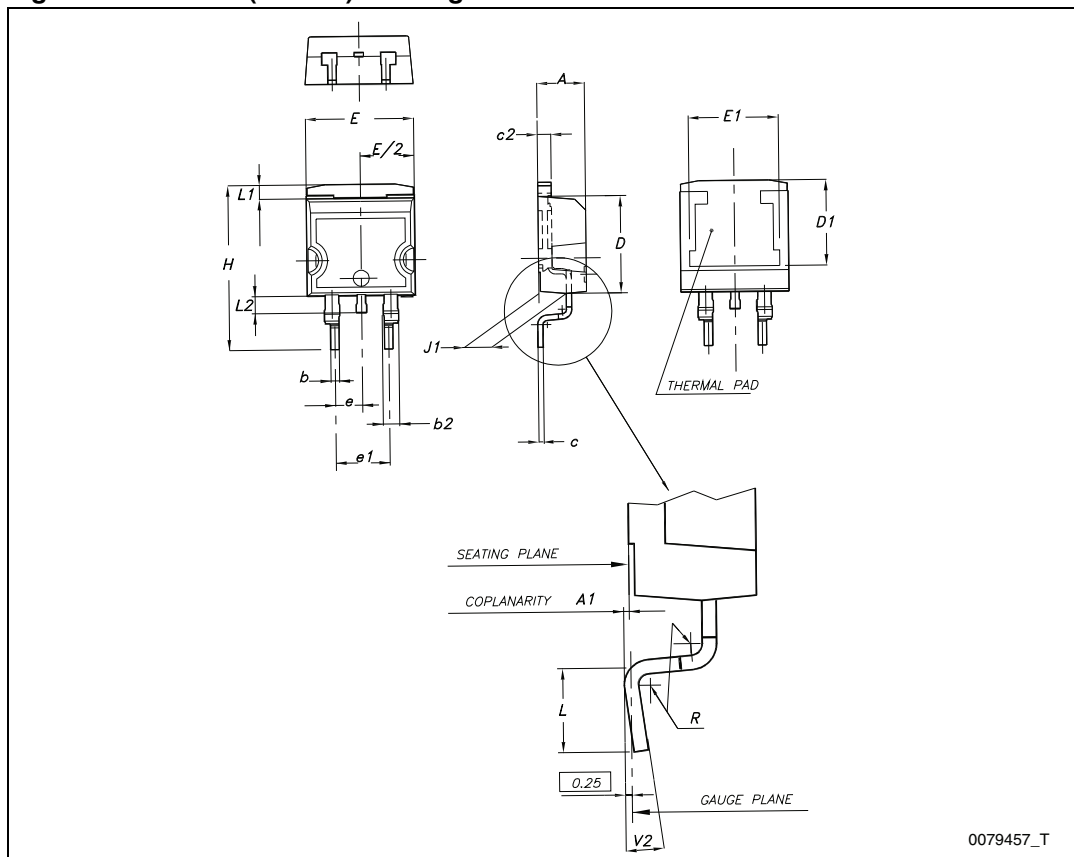
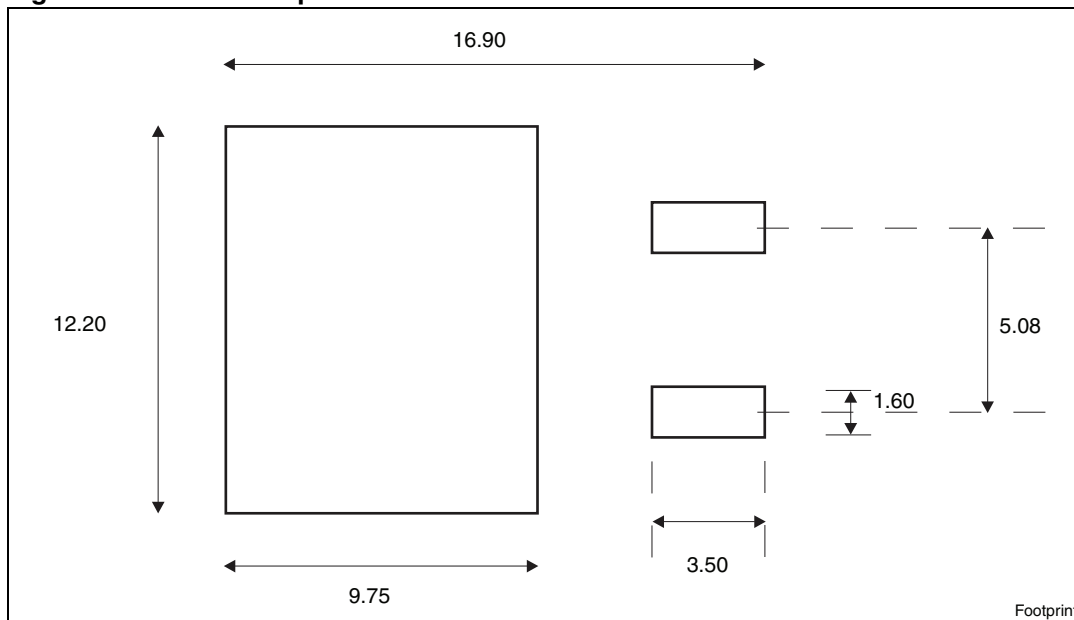


Figure 24. D<sup>2</sup>PAK footprint<sup>(a)</sup>

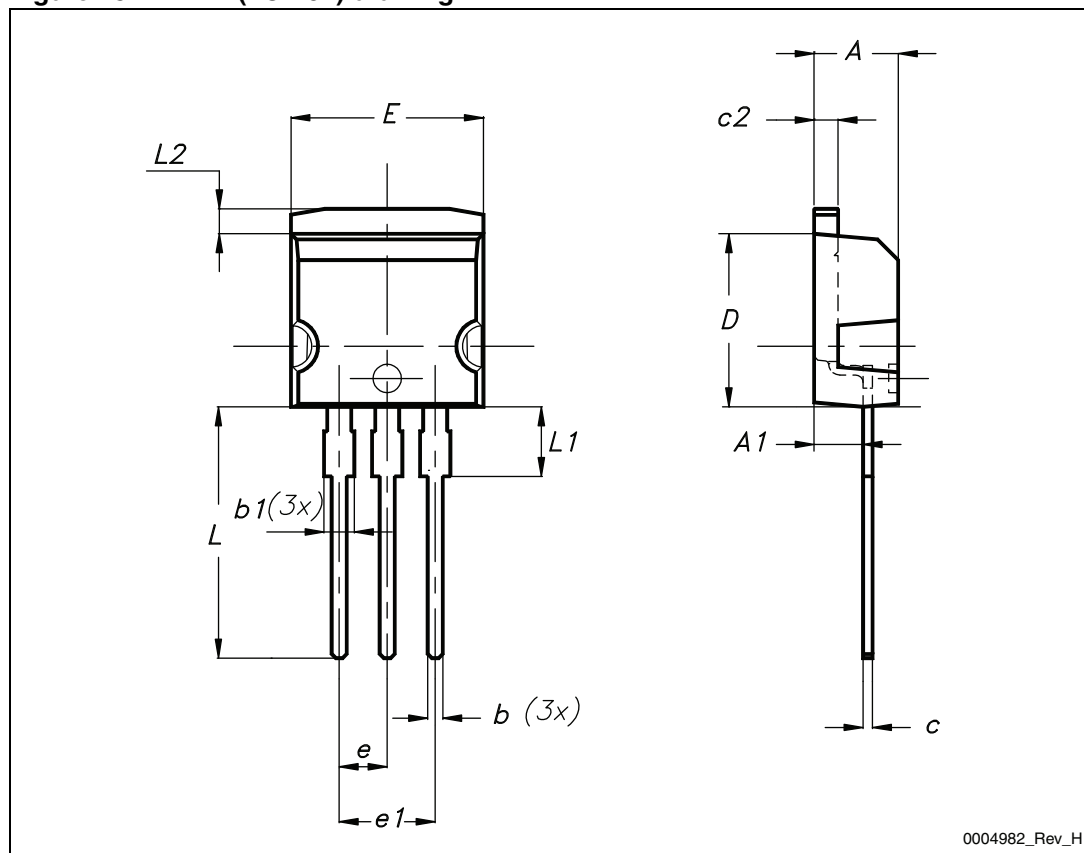


a. All dimension are in millimeters

Table 10. I<sup>2</sup>PAK (TO-262) mechanical data

DIM.	mm.		
	min.	typ	max.
A	4.40		4.60
A1	2.40		2.72
b	0.61		0.88
b1	1.14		1.70
c	0.49		0.70
c2	1.23		1.32
D	8.95		9.35
e	2.40		2.70
e1	4.95		5.15
E	10		10.40
L	13		14
L1	3.50		3.93
L2	1.27		1.40

Figure 25. I<sup>2</sup>PAK (TO-262) drawing



0004982\_Rev\_H



Table 11. TO-220 type A mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.40		4.60
b	0.61		0.88
b1	1.14		1.70
c	0.48		0.70
D	15.25		15.75
D1		1.27	
E	10		10.40
e	2.40		2.70
e1	4.95		5.15
F	1.23		1.32
H1	6.20		6.60
J1	2.40		2.72
L	13		14
L1	3.50		3.93
L20		16.40	
L30		28.90	
ØP	3.75		3.85
Q	2.65		2.95

Figure 26. TO-220 type A drawing

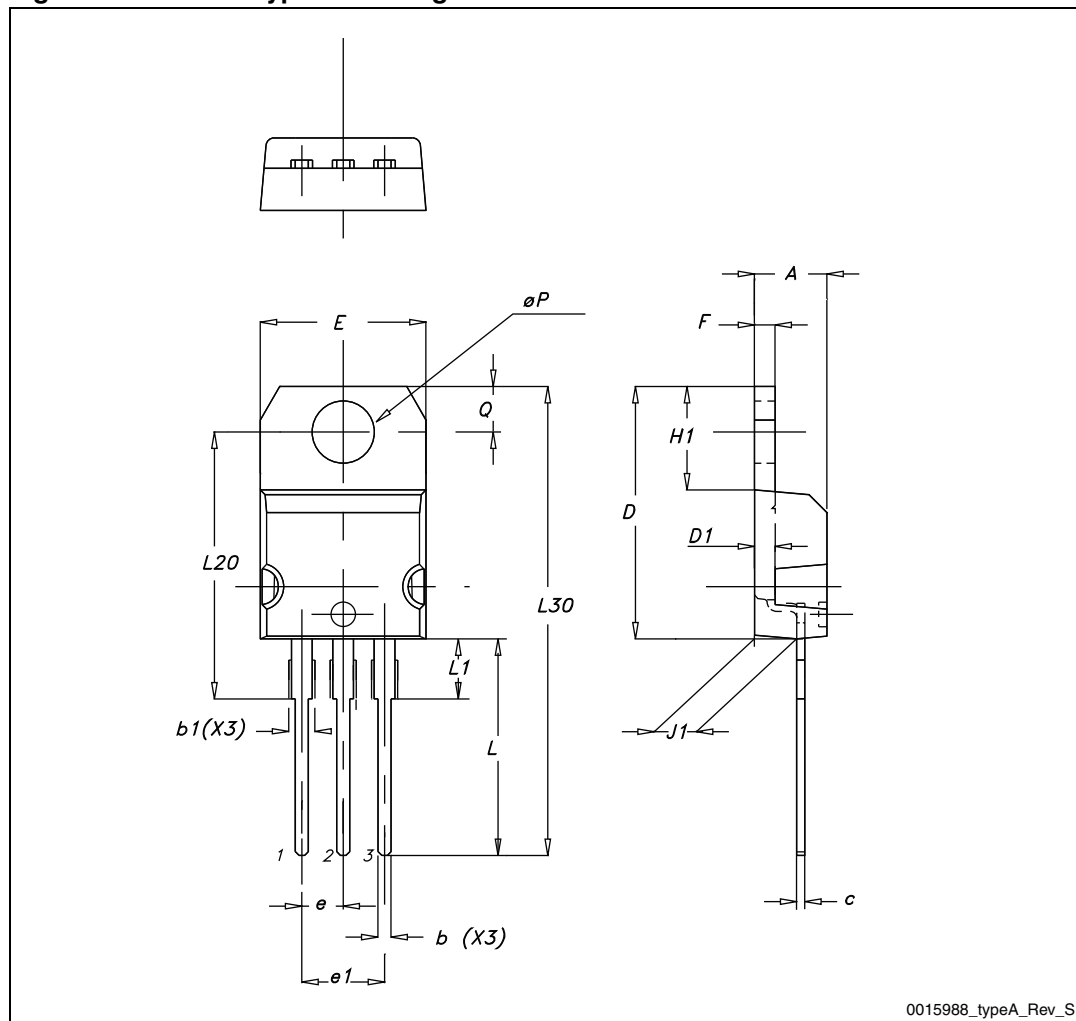
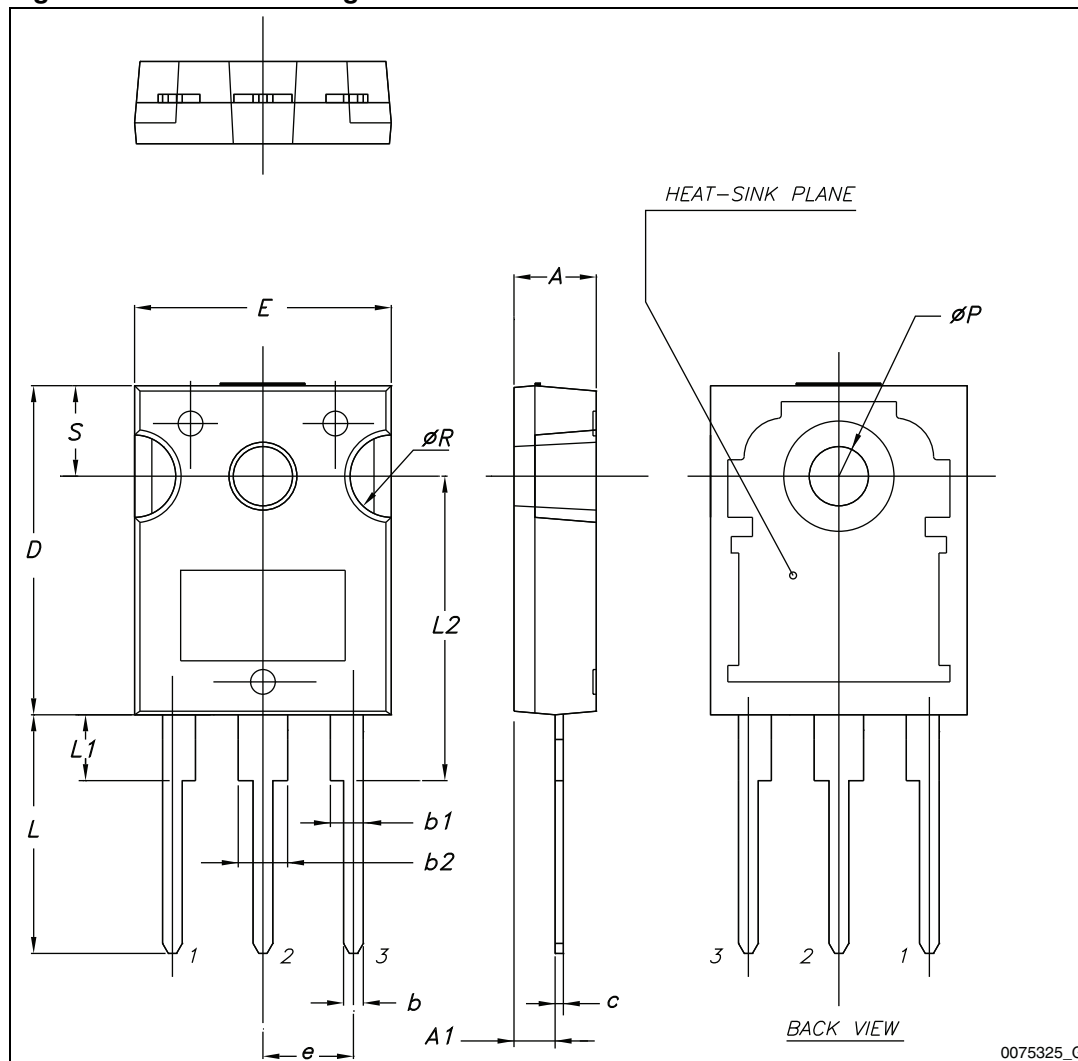


Table 12. TO-247 mechanical data

Dim.	mm.		
	Min.	Typ.	Max.
A	4.85		5.15
A1	2.20		2.60
b	1.0		1.40
b1	2.0		2.40
b2	3.0		3.40
c	0.40		0.80
D	19.85		20.15
E	15.45		15.75
e	5.30	5.45	5.60
L	14.20		14.80
L1	3.70		4.30
L2		18.50	
ØP	3.55		3.65
ØR	4.50		5.50
S	5.30	5.50	5.70

Figure 27. TO-247 drawing

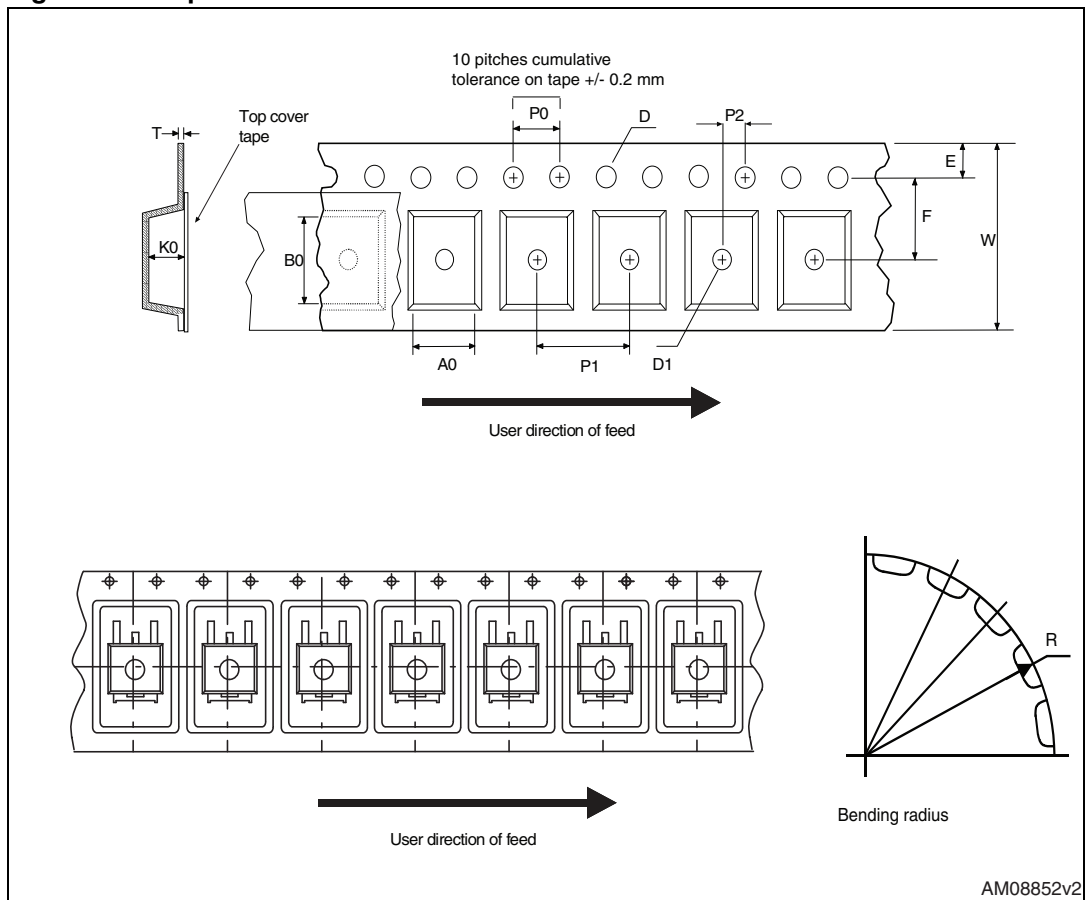


## 5 Packaging mechanical data

Table 13. D<sup>2</sup>PAK (TO-263) tape and reel mechanical data

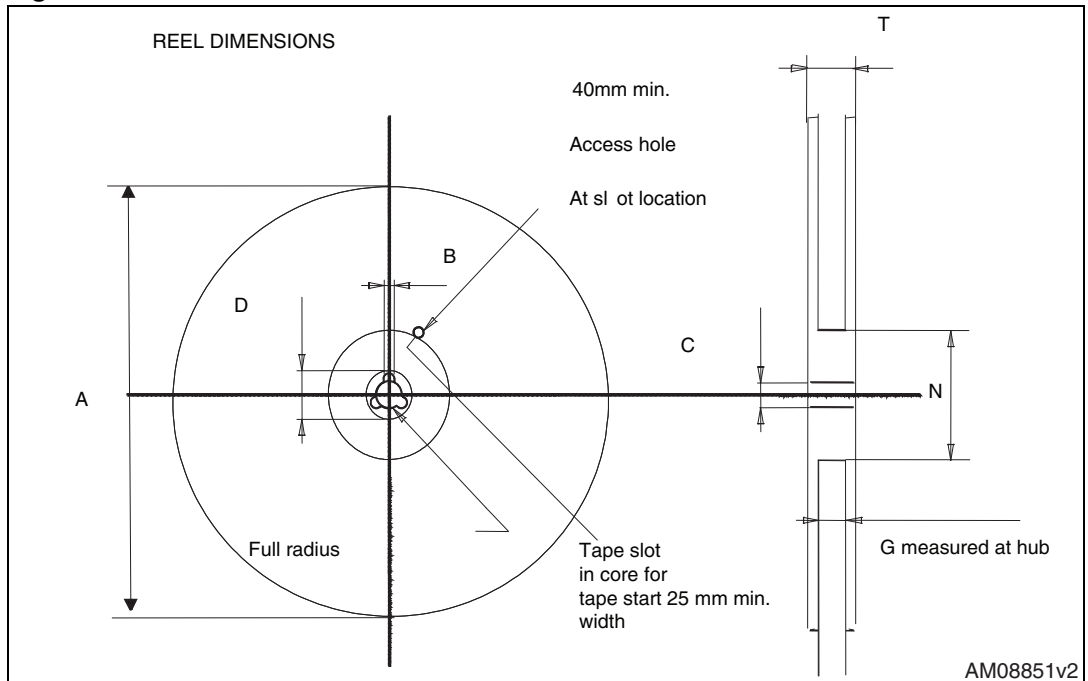
Tape			Reel		
Dim.	mm		Dim.	mm	
	Min.	Max.		Min.	Max.
A0	10.5	10.7	A		330
B0	15.7	15.9	B	1.5	
D	1.5	1.6	C	12.8	13.2
D1	1.59	1.61	D	20.2	
E	1.65	1.85	G	24.4	26.4
F	11.4	11.6	N	100	
K0	4.8	5.0	T		30.4
P0	3.9	4.1			
P1	11.9	12.1		Base qty	1000
P2	1.9	2.1		Bulk qty	1000
R	50				
T	0.25	0.35			
W	23.7	24.3			

Figure 28. Tape



AM08852v2

Figure 29. Reel



AM08851v2



## 6 Revision history

Table 14. Document revision history

Date	Revision	Changes
06-Mar-2012	1	First release.
01-Feb-2013	2	<ul style="list-style-type: none"><li>– The part numbers STF20N65M5 and STFI20N65M5 have been moved to a separate datasheet.</li><li>– Added: part numbers STB20N65M5 and STI20N65M5</li><li>– Modified: <a href="#">note 1</a> on <a href="#">Table 2</a>, <a href="#">Table 4</a> values and typical values of <a href="#">Table 5</a>, <a href="#">6</a>, <a href="#">7</a>, <a href="#">8</a></li><li>– Added: <math>R_{thj-pcb}</math> and <a href="#">note 1</a> on <a href="#">Table 3</a></li><li>– Updated: <a href="#">Section 4: Package mechanical data</a></li><li>– Added: <a href="#">Section 2.1: Electrical characteristics (curves)</a></li></ul>

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